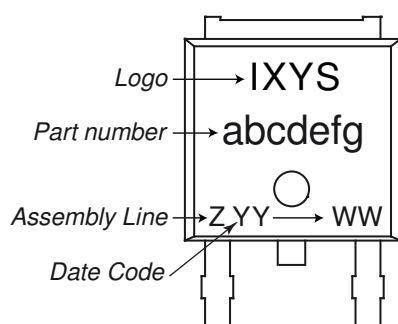


Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				150	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				150	V
I_R	reverse current, drain current	$V_R = 150\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			250	μA
		$V_R = 150\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$			2.5	mA
V_F	forward voltage drop	$I_F = 6\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			0.78	V
		$I_F = 12\text{ A}$				0.86	V
		$I_F = 6\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			0.62	V
		$I_F = 12\text{ A}$				0.71	V
I_{FAV}	average forward current	$T_C = 165^{\circ}\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 175^{\circ}\text{C}$			6	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^{\circ}\text{C}$		0.45	V
r_F	slope resistance					14.6	m Ω
R_{thJC}	thermal resistance junction to case					3	K/W
R_{thCH}	thermal resistance case to heatsink				0.50		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				50	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$	$T_{VJ} = 45^{\circ}\text{C}$			120	A
C_J	junction capacitance	$V_R = 24\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		82		pF

Package TO-252 (DPak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			20	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				0.3		g
F_C	mounting force with clip		20		60	N

¹⁾ I_{RMS} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

Product Marking

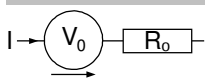


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSS6-015AS	6Y150AS	Tape & Reel	2500	498912

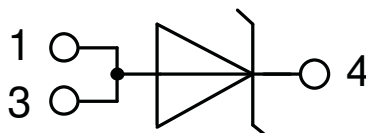
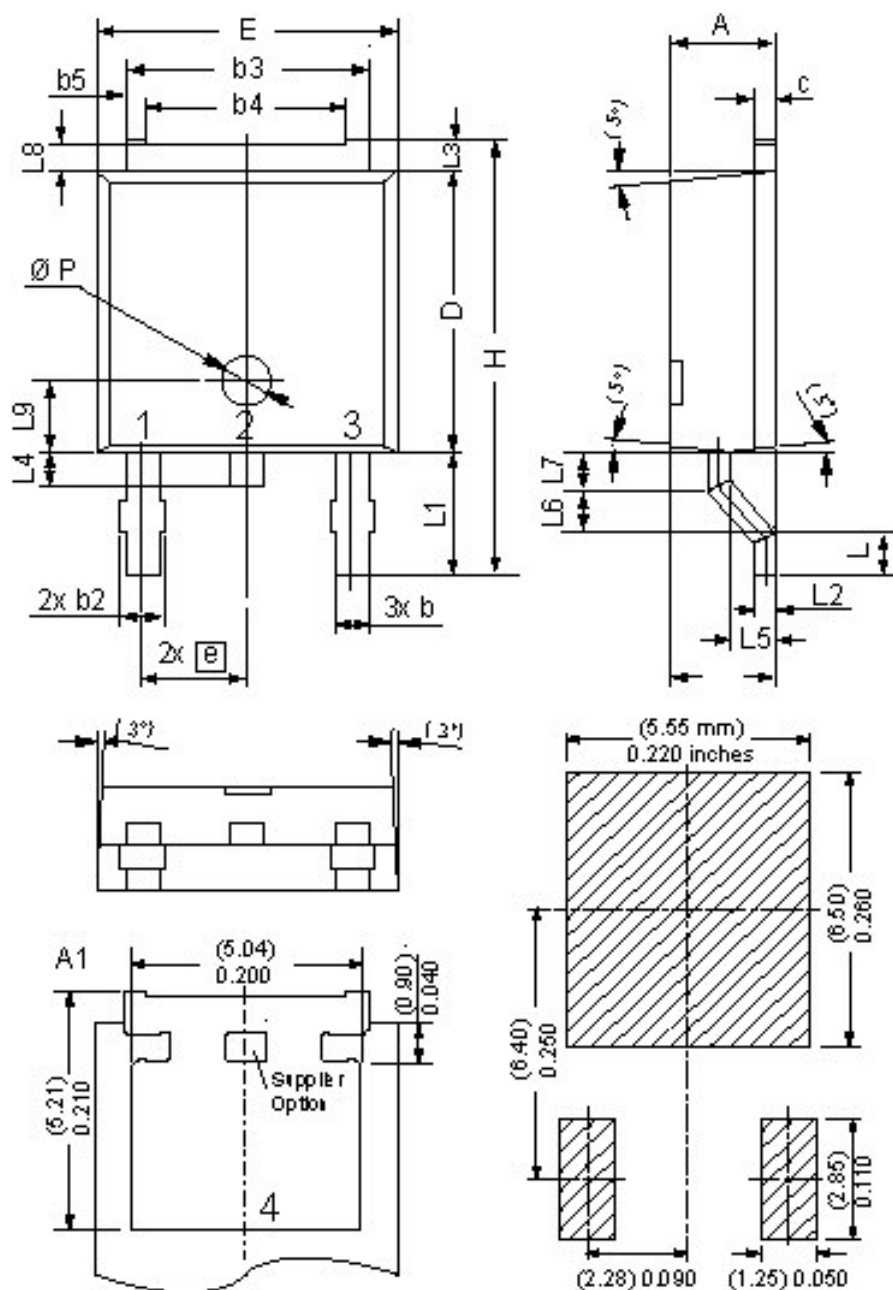
Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 175\text{ °C}$

			Schottky
$V_{0\text{ max}}$	threshold voltage	0.45	V
$R_{0\text{ max}}$	slope resistance *	11.4	mΩ

Outlines TO-252 (DPak)



Schottky

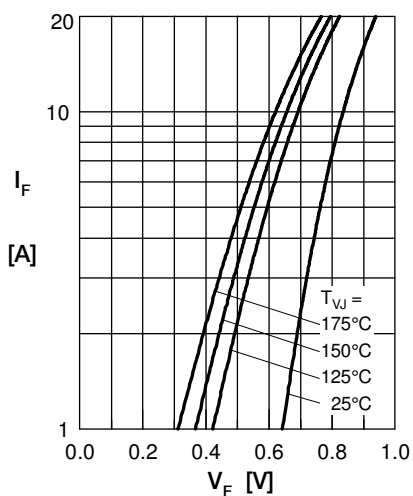


Fig. 1 Max. forward voltage drop characteristics

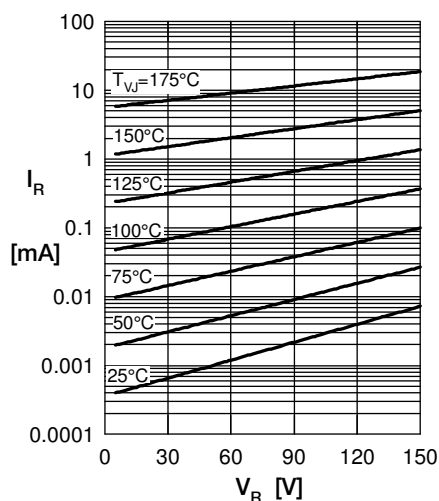


Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

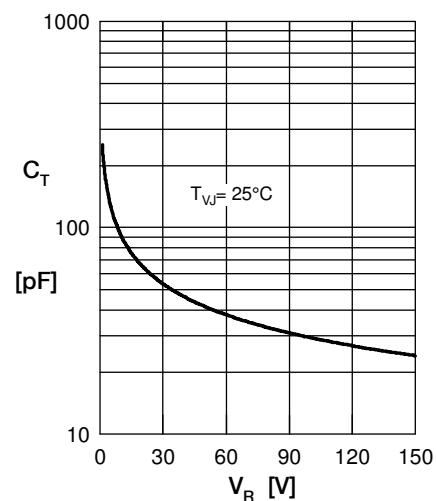


Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

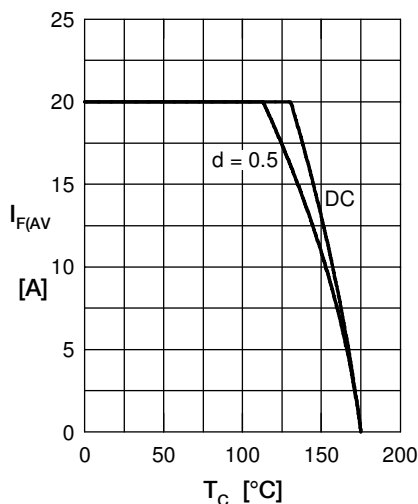


Fig. 4 Average forward current $I_{F(AV)}$ vs. case temp. T_C

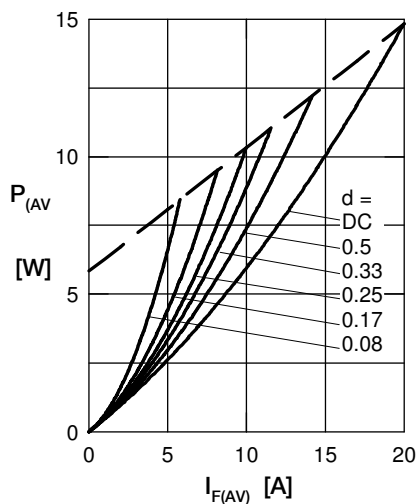


Fig. 5 Forward power loss characteristics

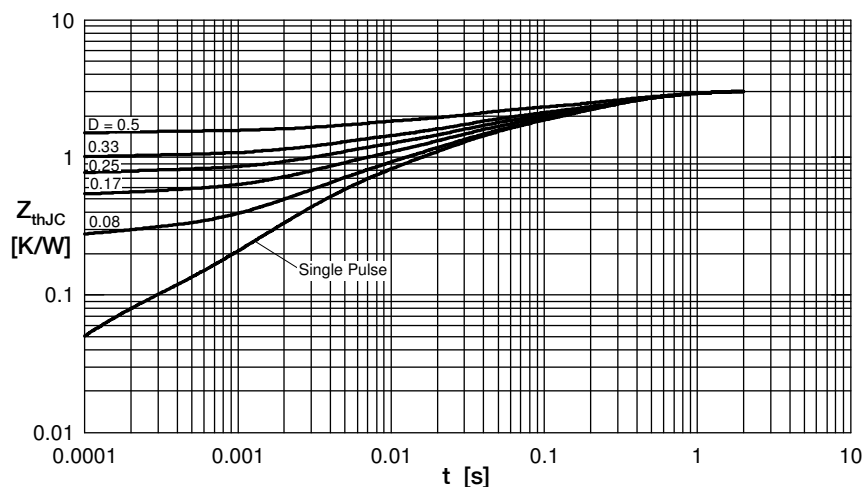


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode